



IMPORTANCE OF CERAMIC SUBSTRATES WITH LOW THERMAL EXPANSION COEFFICIENT IN SEMICONDUCTOR WAFER TESTING



Stand up with
Electro Material Ceramic
and Solution

PROBE TODAY, FOR TOMORROW
2023 CONFERENCE

Jung Hwan Cho, Dae Hyeong Lee, Doo Yun Chung, Chi Seung In,
Seung Ho Han, Hun Tae Kim, Yu Jin Choi, SEMCNS.INC

Introduction

*STF : Space Transformer

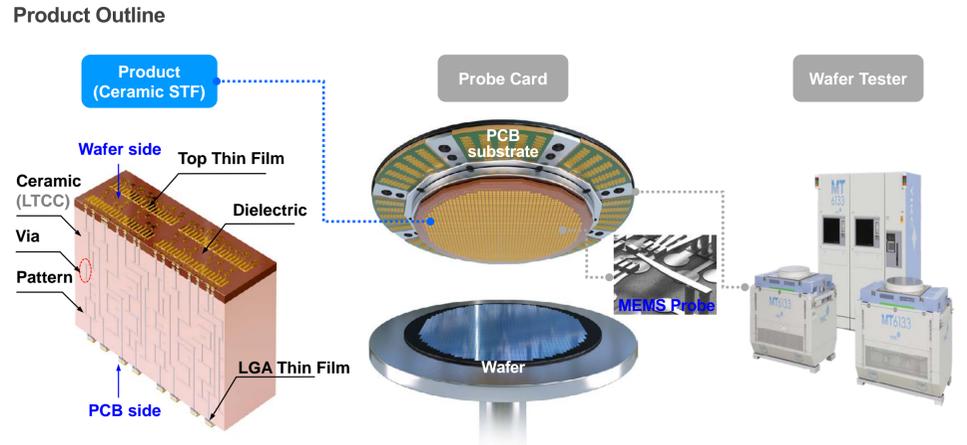
- SEMCNS provides a solution for large area STF* products using LTCC materials for semiconductor wafer inspection processes.



Main Product
Ceramic STF for Semiconductor Wafer Inspection Process

Key Technology
100% in-house Continuous line manufacturing

- Ceramic Technology**
The strength, electrical connectivity and position precision of ceramic STF
- Grinding Technology**
Adapt to high quality thin film, customer optimal shape implementation
- Thin Film Technology**
Development of multi-layered thin film technology suitable for customer's process
- Design Technology**
Suitable for customer's design requested by SEMCNS's own Design technology

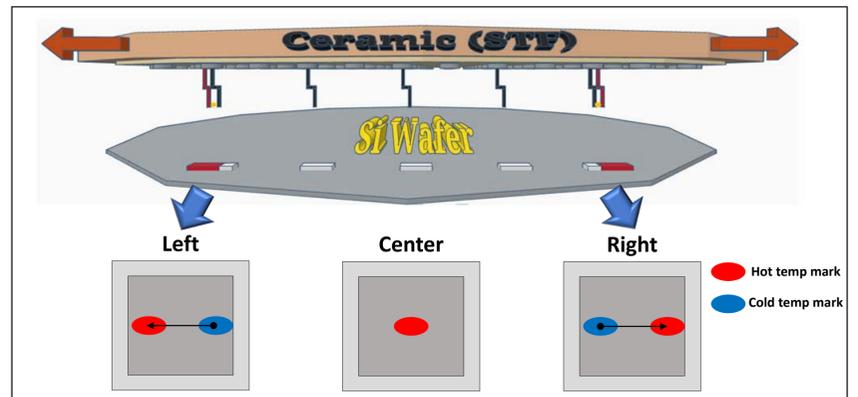


* CTE : Coefficient of Thermal Expansion

- Pin scrub occurs on the wafer pad during the wafer testing, which is caused by the difference in CTE* of wafer and STF.
- Recently, precise control of pin scrub is required and market trend needs a Low CTE material.
- There are three reasons why Low CTE material is needed for semiconductor Probe Cards.

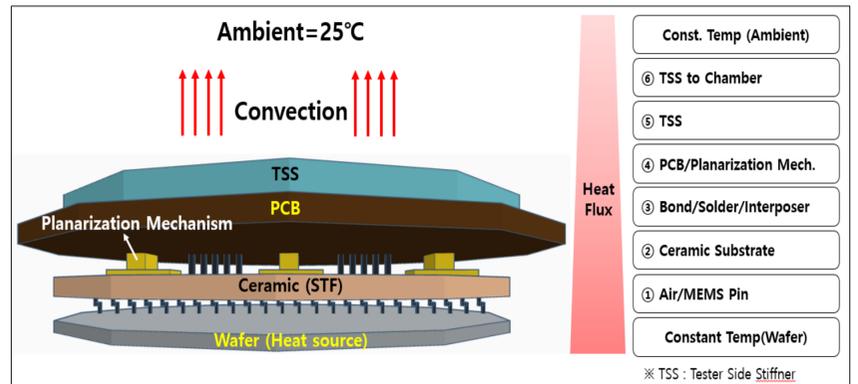
1) There are increasing adoptions of automotive parts and environmental temperature is increasing.

Test Temperature	Normal	Automotive
Cold Temp.(°C)	-25	-50
Hot Temp. (°C)	+95	+125



2) The # of Probe Pins is increasing due to an increase in the Parallelism of wafers.

Pins	Normal	High Density
# of Pins (K)	1x	2x ~ 3x



3) The pad size for semiconductors is reducing.

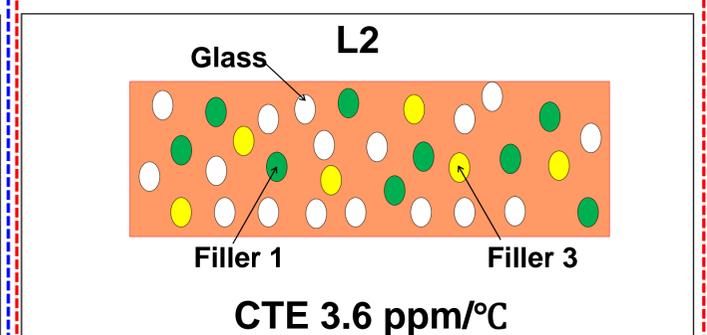
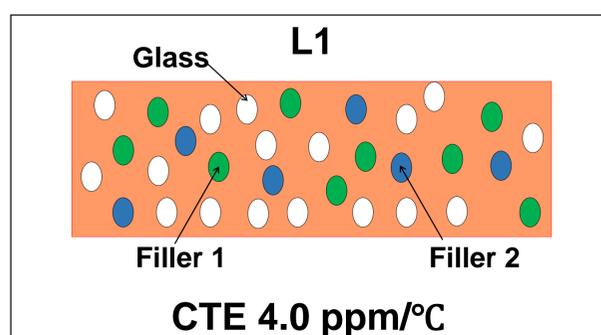
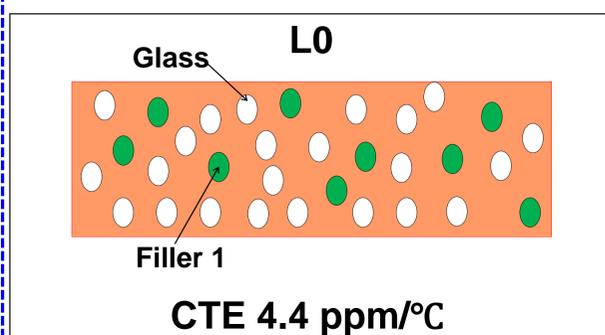
Pad	Present	Near future
Pad Size (µm)	62.5 x 60	50 x 50

Approach

- Producing and developing STF using LTCC materials with three different CTE values.
 - L0 : Crystallization Glass + Filler 1 → CTE 4.4 ppm/°C (Mass-production)
 - L1 : Crystallization Glass + Filler 1 + Filler 2 (Low CTE) → CTE 4.0 ppm/°C (Mass-production)
 - L2 : Crystallization Glass + Filler 1 + Filler 3 (Low CTE) → CTE 3.6 ppm/°C (Under Development, ~2024)

Mass Product

Under development



• **Results**

- The characteristics of the LTCC material on mass-production are as follows.

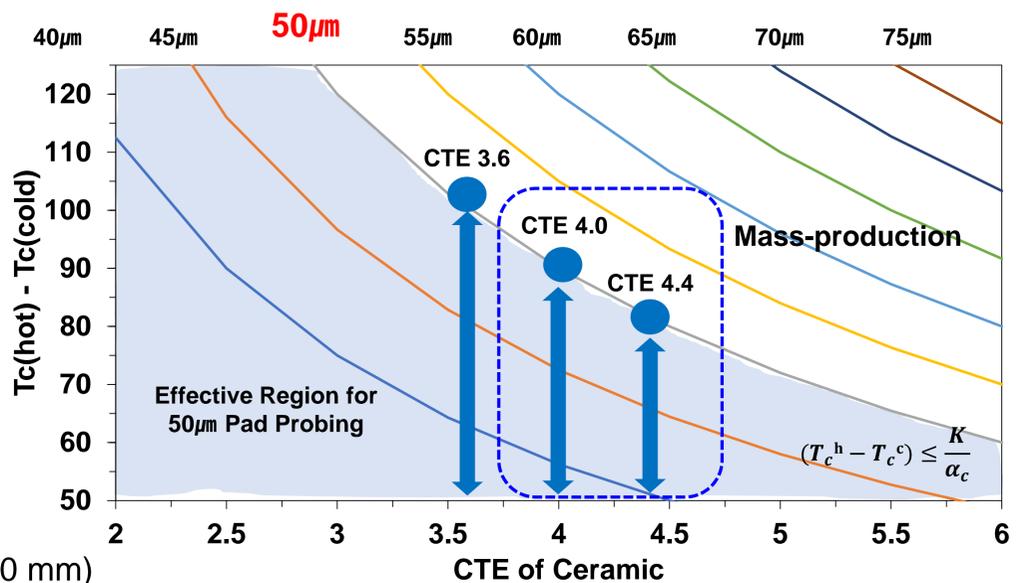
	CTE at 25~100°C (ppm/°C)	Dielectric Constant at @1MHz	Dielectric Loss at @1MHz	Modulus (MPa)	Thermal Conductivity (W/m-K)	Specific Heat (J/g·K)
L0	4.4	7.73	0.0019	117	2.28	0.749
L1	4.0	7.40	0.0025	118	1.97	0.748

※ The CTE value was measured on a 12-inch STF using 3D vision measurement. (25~100°C)

- Using the L1 materials, it can provide a CTE of 3.87ppm/°C at 25°C~100°C and CTE of 3.60ppm/°C at -40°C~140°C.

* TMA : ThermoMechanical Analysis

Temp. Range (°C)	TMA* CTE (ppm/°C)	
	SEMCNS LTCC	
	L0	L1
25~100	4.36	3.87
-40~120	4.19	3.49
-40~140	4.27	3.60

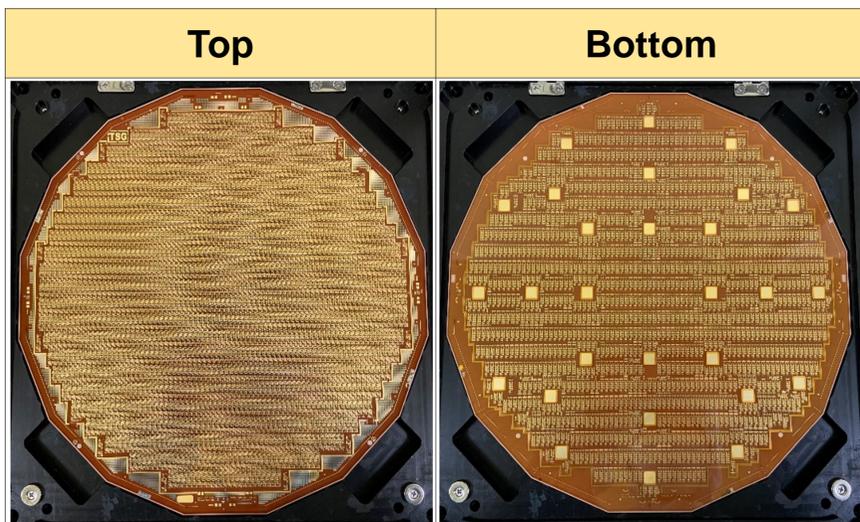


※ The CTE value was measured by TMA (5 x 5 x 20 mm)

※ Credit : 2013 SWTW by Y.H.Park

- Producing a variety of product using L0 and L1 materials.
- As the CTE is decreasing, it is being developed to respond to high-spec and diverse products.

* CIS : CMOS Image Sensor



12" DRAM	12" NAND	CIS* / Parametric
Total Pin : 60K ~ 100K Ceramic Inner Layer : 15 ~ 35 Thin film Layer : 5	Total Pin : 10K ~ 63K Ceramic Inner Layer : 10 ~ 43 Thin film Layer : 2	Total Pin : 30K ~ 40K Ceramic Inner Layer : 40 ~ 80 Thin Film Layer : 2

• **Conclusion**

- Develop Low CTE materials (L1) about CTE 4.0ppm/°C.
- Improved pin scrub using L1 materials.
- CTE 4.4 and 4.0ppm/°C are currently in mass production.
- CTE 3.6ppm/°C is under development. (~2024)

• **Contact Information**

- dooyun.chung@semcns.com (South Korea)
- jhcho@semcns.com (South Korea)
- shhan@semcns.com (South Korea)